

# Switching Diode, High Voltage, High Temperature

## BASH19L Series

### Features

- 175°C  $T_{J(MAX)}$  – Rated for High Temperature, Mission Critical Applications
- NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Continuous Reverse Voltage	$V_R$	120 200 250	Vdc	
				BASH19
				BASH20
				BASH21
Repetitive Peak Reverse Voltage	$V_{RRM}$	120 200 250	Vdc	
				BASH19
				BASH20
				BASH21
Continuous Forward Current	$I_F$	200	mAdc	
Peak Forward Surge Current (1/2 Cycle, Sine Wave, 60 Hz)	$I_{FSM}$	2	A	
Repetitive Peak Forward Current (Pulse Train: $T_{ON} = 1$ s, $T_{OFF} = 0.5$ s)	$I_{FRM}$	0.6	A	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	°C	
Electrostatic Discharge	ESD	HM < 500	V	
		MM < 400	V	

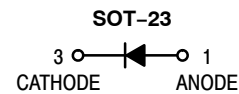
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



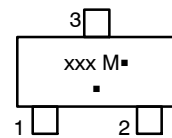
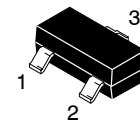
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## HIGH VOLTAGE SWITCHING DIODE



### MARKING DIAGRAM



**SOT-23 (TO-236)  
CASE 318  
STYLE 8**

AD7 = BASH19L  
AC7 = BASH20L  
AA7 = BASH21L  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# BASH19L Series

## THERMAL CHARACTERISTICS

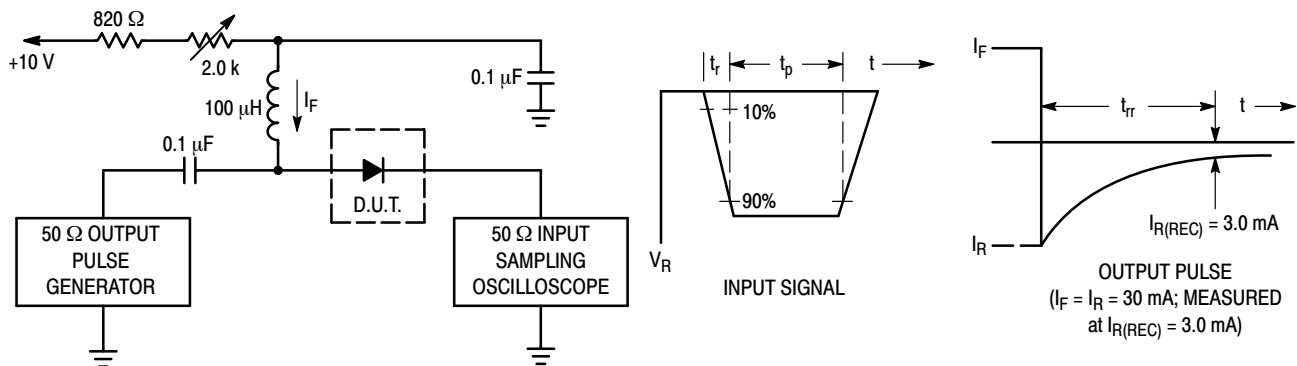
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (SOT-23)	$R_{\theta JA}$	340	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	400	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$

- FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current ( $V_R = 100$ Vdc) ( $V_R = 150$ Vdc) ( $V_R = 200$ Vdc) ( $V_R = 100$ Vdc, $T_J = 175^\circ\text{C}$ ) ( $V_R = 150$ Vdc, $T_J = 175^\circ\text{C}$ ) ( $V_R = 200$ Vdc, $T_J = 175^\circ\text{C}$ )	$I_R$	-	0.1	$\mu\text{A}$ dc
	BASH19	-	0.1	
	BASH20	-	0.1	
	BASH21	-	0.1	
	BASH19	-	100	
	BASH20	-	100	
	BASH21	-	100	
Reverse Breakdown Voltage ( $I_{BR} = 100$ $\mu\text{A}$ dc) ( $I_{BR} = 100$ $\mu\text{A}$ dc) ( $I_{BR} = 100$ $\mu\text{A}$ dc)	$V_{(BR)}$	120	-	Vdc
	BASH19	200	-	
	BASH20	250	-	
	BASH21	-	-	
Forward Voltage ( $I_F = 100$ mAdc) ( $I_F = 200$ mAdc)	$V_F$	-	1.0	Vdc
		-	1.25	
Diode Capacitance ( $V_R = 0$ , $f = 1.0$ MHz)	$C_D$	-	5.0	pF
Reverse Recovery Time ( $I_F = I_R = 30$ mA, $I_{R(REC)} = 3.0$ mA, $R_L = 100$ )	$t_{rr}$	-	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



- A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 30 mA.
- Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 30 mA.
- $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

# BASH19L Series

## TYPICAL CHARACTERISTICS

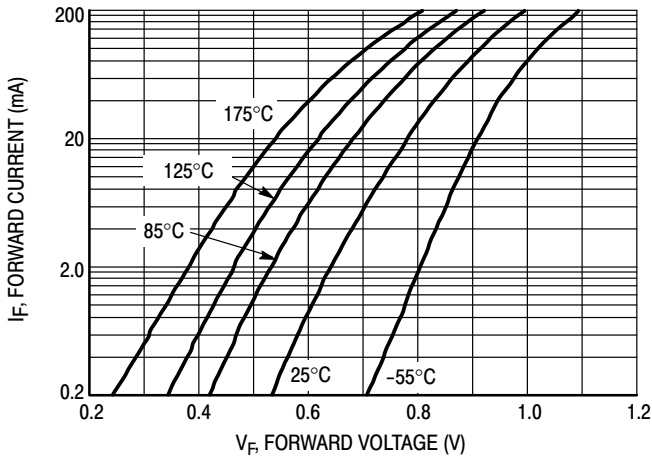


Figure 2. Forward Voltage

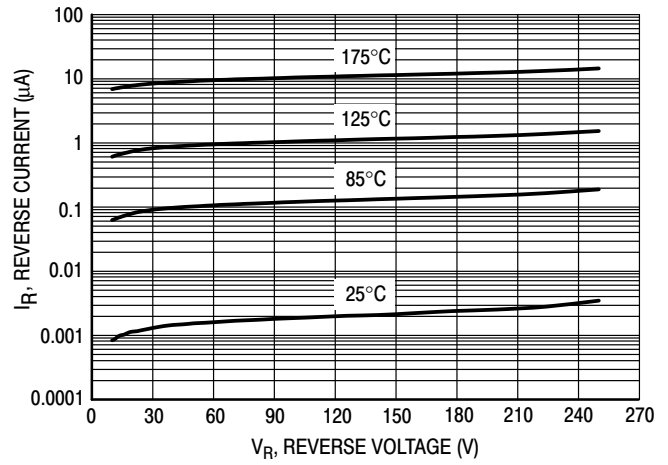


Figure 3. Leakage Current

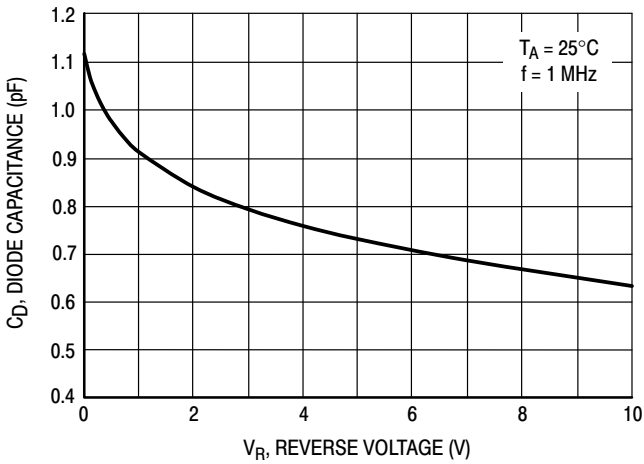


Figure 4. Capacitance

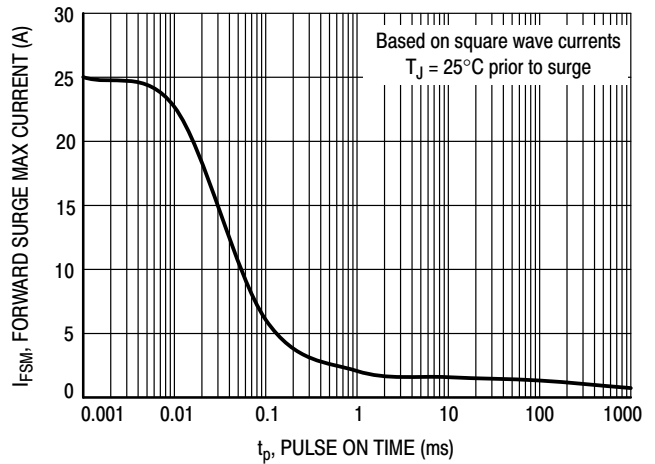


Figure 5. Forward Surge Current

## BASH19L Series

### ORDERING INFORMATION

Device	Package	Shipping†
BASH19LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBASH19LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BASH20LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBASH20LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BASH21LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBASH21LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel

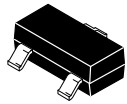
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable – release available upon request.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

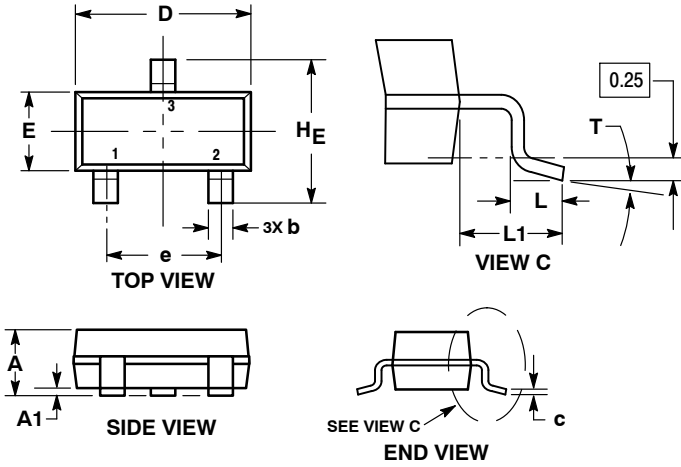
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**SOT-23 (TO-236)**  
CASE 318-08  
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- |   |   |   |  |
|---|---|---|--|
| STYLE 1 THRU 5:<br>CANCELLED                                | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR       | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE           | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE      |
| STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          | STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE          | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE      |
| STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE         |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN           | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT         | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE          |
| STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION | STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE          |

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<b>DESCRIPTION:</b>	<b>SOT-23 (TO-236)</b>	<b>PAGE 1 OF 1</b>

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